

TM16EN64HPU, TM16EN64LPU 16777216 BY 64-BIT TM16EN72HPU, TM16EN72LPU 16777216 BY 72-BIT EXTENDED-DATA-OUT DYNAMIC RAM MODULES

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- **Organization**
 - TM16EN64xPU-xx . . . 16777216 × 64 Bits
 - TM16EN72xPU-xx . . . 16777216 × 72 Bits
- **Single 3.3-V Power Supply** (±10% Tolerance)
- **JEDEC 168-Pin Dual-In-Line Memory Module (DIMM) Without Buffer for Use With Socket**
- **TM16EN64HPUxx — Utilizes Sixteen 64M-Bit High-Speed (16M×4-Bit) Dynamic RAMs**
- **TM16EN72HPUxx — Utilizes Eighteen 64M-Bit High-Speed (16M×4-Bit) Dynamic RAMs**
- **High-Speed, Low-Noise LVTTTL Interface**
- **High-Reliability 32-Lead 300-Mil-Wide Surface-Mount Thin Small-Outline Package (TSOP) (DGC Suffix)**
- **Long Refresh Periods:**
 - TM16ENxxHPU: 64 ms (4096 Cycles)
 - TM16ENxxLPU: 64 ms (8192 Cycles)
- **3-State Output**
- **Extended-Data-Out (EDO) Operation With $\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ (CBR), $\overline{\text{RAS}}$ -Only, and Hidden Refresh**
- **Serial Presence-Detect (SPD) Using EEPROM**
- **Ambient Temperature Range** 0°C to 70°C
- **Gold-Plated Contacts**
- **Performance Ranges**

	ACCESS TIME	ACCESS TIME	ACCESS TIME	EDO CYCLE
	t _{RAC} (MAX)	t _{CAC} (MAX)	t _{AA} (MAX)	t _{HPC} (MIN)
'16ENxxxPU-40	40 ns	11 ns	20 ns	16 ns
'16ENxxxPU-50	50 ns	13 ns	25 ns	20 ns
'16ENxxxPU-60	60 ns	15 ns	30 ns	25 ns

description

The TM16EN64HPU is a 128M-byte, 168-pin, dual-in-line memory module (DIMM). The DIMM is composed of sixteen TMS465409, 16777216 × 4-bit 4K-refresh EDO dynamic random-access memories (DRAMs), each in a 400-mil, 32-pin plastic thin small-outline package (TSOP) (DGC suffix) mounted on a substrate with decoupling capacitors. See the TMS465409 data sheet (literature number SMKS895).

The TM16EN64LPU is a 128M-byte, 168-pin DIMM. The DIMM is composed of eighteen TMS464409, 16777216 × 4-bit 8K-refresh EDO dynamic random-access memories (DRAMs), each in a 400-mil, 32-pin plastic TSOP (DGC suffix) mounted on a substrate with decoupling capacitors. See the TMS465409 data sheet (literature number SMKS895).

The TM16EN72HPU is a 128M-byte, 168-pin DIMM. The DIMM is composed of eighteen TMS465409, 16777216 × 4-bit 4K-refresh EDO dynamic random-access memories (DRAMs), each in a 400-mil, 32-pin plastic TSOP (DGC suffix) mounted on a substrate with decoupling capacitors. See the TMS465409 data sheet (literature number SMKS895).

The TM16EN72LPU is a 128M-byte, 168-pin DIMM. The DIMM is composed of eighteen TMS464409, 4194309 × 4-bit 8K-refresh EDO dynamic random-access memories (DRAMs), each in a 400-mil, 32-pin plastic TSOP (DGC suffix) mounted on a substrate with decoupling capacitors. See the TMS465409 data sheet (literature number SMKS895).

operation

The TM16EN64xPU operates as sixteen TMS46x409s that are connected as shown in the TM16EN64xPU functional block diagram. The TM16EN72xPU operates as eighteen TMS46x409s that are connected as shown in the TM16EN72xPU functional block diagram.



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 **TEXAS
INSTRUMENTS**

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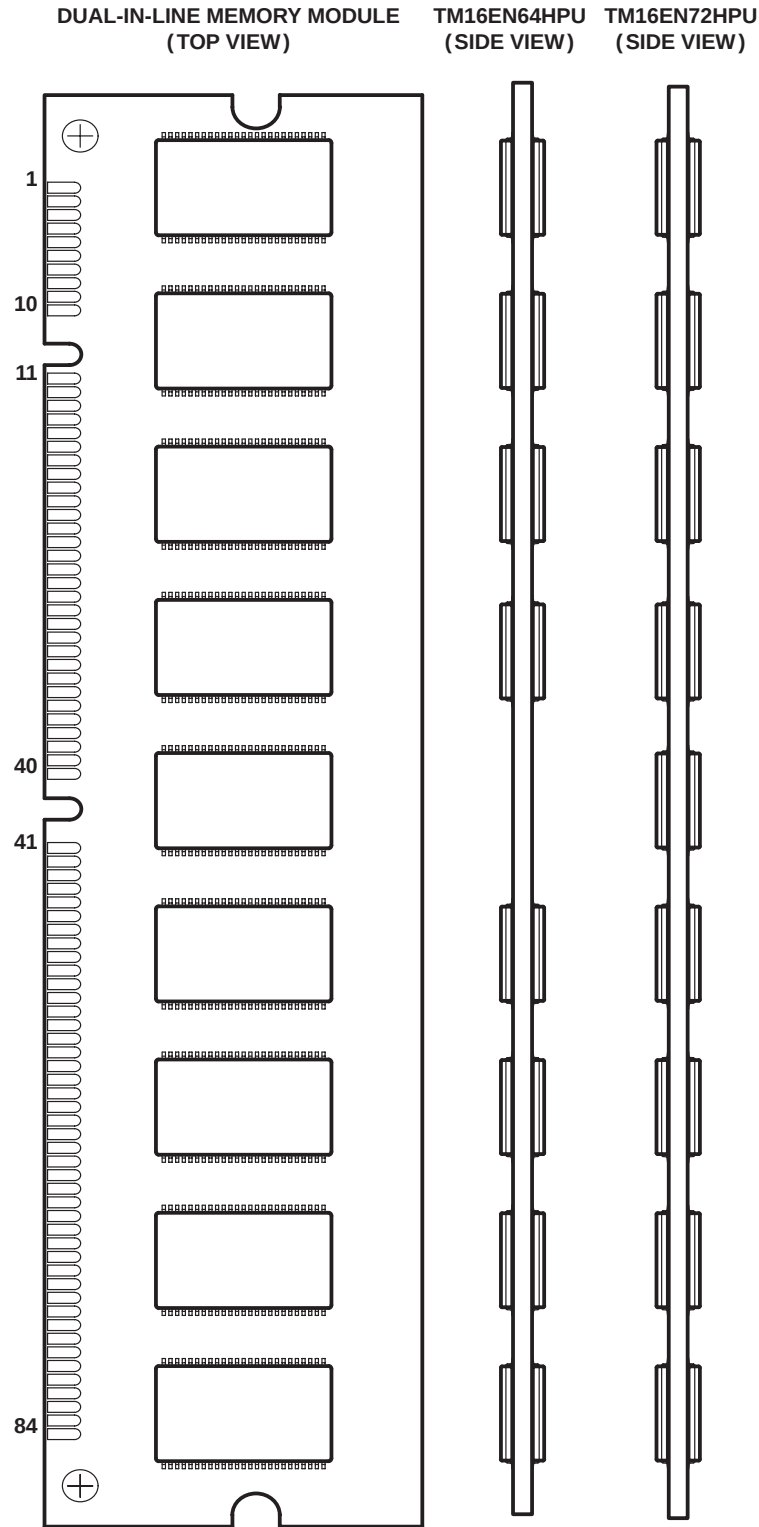
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PIN NOMENCLATURE – TM16ENxxHPU	
A[0:11]	Row Address Inputs
A[0:11]	Column Address Inputs
DQ[0:63]	Data In/Data Out
CB[0:7]	Check Bit In/Check Bit Out
CAS[0:7]	Column-Address Strobe
RAS0 and RAS2	Row-Address Strobe
WE0 and WE2	Write Enable
OE0 and OE2	Output Enable
SA[0:2]	Serial Presence-Detect (SPD)
SDA	SPD Address/Data
SCL	SPD Clock
NC	No-Connect Pin
VDD	3.3-V Supply
VSS	Ground

PIN NOMENCLATURE – TM16ENxxLPU	
A[0:12]	Row Address Inputs
A[0:10]	Column Address Inputs
DQ[0:63]	Data In/Data Out
CB[0:7]	Check Bit In/Check Bit Out
CAS[0:7]	Column-Address Strobe
RAS0 and RAS2	Row-Address Strobe
WE0 and WE2	Write Enable
OE0 and OE2	Output Enable
SA[0:2]	Serial Presence-Detect (SPD)
SDA	SPD Address/Data
SCL	SPD Clock
NC	No-Connect Pin
VDD	3.3-V Supply
VSS	Ground

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Pin Assignments

NO.	PIN NAME	NO.	PIN NAME	NO.	PIN NAME	NO.	PIN NAME
1	V _{SS}	43	V _{SS}	85	V _{SS}	127	V _{SS}
2	DQ0	44	$\overline{\text{OE}}2$	86	DQ32	128	NC
3	DQ1	45	$\overline{\text{RAS}}2$	87	DQ33	129	NC
4	DQ2	46	$\overline{\text{CAS}}2$	88	DQ34	130	$\overline{\text{CAS}}6$
5	DQ3	47	$\overline{\text{CAS}}3$	89	DQ35	131	$\overline{\text{CAS}}7$
6	V _{DD}	48	$\overline{\text{WE}}2$	90	V _{DD}	132	NC
7	DQ4	49	V _{DD}	91	DQ36	133	V _{DD}
8	DQ5	50	NC	92	DQ37	134	NC
9	DQ6	51	NC	93	DQ38	135	NC
10	DQ7	52	CB2	94	DQ39	136	CB6
11	DQ8	53	CB3	95	DQ40	137	CB7
12	V _{SS}	54	V _{SS}	96	V _{SS}	138	V _{SS}
13	DQ9	55	DQ16	97	DQ41	139	DQ48
14	DQ10	56	DQ17	98	DQ42	140	DQ49
15	DQ11	57	DQ18	99	DQ43	141	DQ50
16	DQ12	58	DQ19	100	DQ44	142	DQ51
17	DQ13	59	V _{DD}	101	DQ45	143	V _{DD}
18	V _{DD}	60	DQ20	102	V _{DD}	144	DQ52
19	DQ14	61	NC	103	DQ46	145	NC
20	DQ15	62	NC	104	DQ47	146	NC
21	CB0	63	NC	105	CB4	147	NC
22	CB1	64	V _{SS}	106	CB5	148	V _{SS}
23	V _{SS}	65	DQ21	107	V _{SS}	149	DQ53
24	NC	66	DQ22	108	NC	150	DQ54
25	NC	67	DQ23	109	NC	151	DQ55
26	V _{DD}	68	V _{SS}	110	V _{DD}	152	V _{SS}
27	$\overline{\text{WE}}0$	69	DQ24	111	NC	153	DQ56
28	$\overline{\text{CAS}}0$	70	DQ25	112	$\overline{\text{CAS}}4$	154	DQ57
29	$\overline{\text{CAS}}1$	71	DQ26	113	$\overline{\text{CAS}}5$	155	DQ58
30	$\overline{\text{RAS}}0$	72	DQ27	114	NC	156	DQ59
31	$\overline{\text{OE}}0$	73	V _{DD}	115	NC	157	V _{DD}
32	V _{SS}	74	DQ28	116	V _{SS}	158	DQ60
33	A0	75	DQ29	117	A1	159	DQ61
34	A2	76	DQ30	118	A3	160	DQ62
35	A4	77	DQ31	119	A5	161	DQ63
36	A6	78	V _{SS}	120	A7	162	V _{SS}
37	A8	79	NC	121	A9	163	NC
38	A10	80	NC	122	A11	164	NC
39	A12	81	NC	123	NC	165	SA0
40	V _{DD}	82	SDA	124	V _{DD}	166	SA1
41	NC	83	SCL	125	NC	167	SA2
42	NC	84	V _{DD}	126	NC	168	V _{DD}

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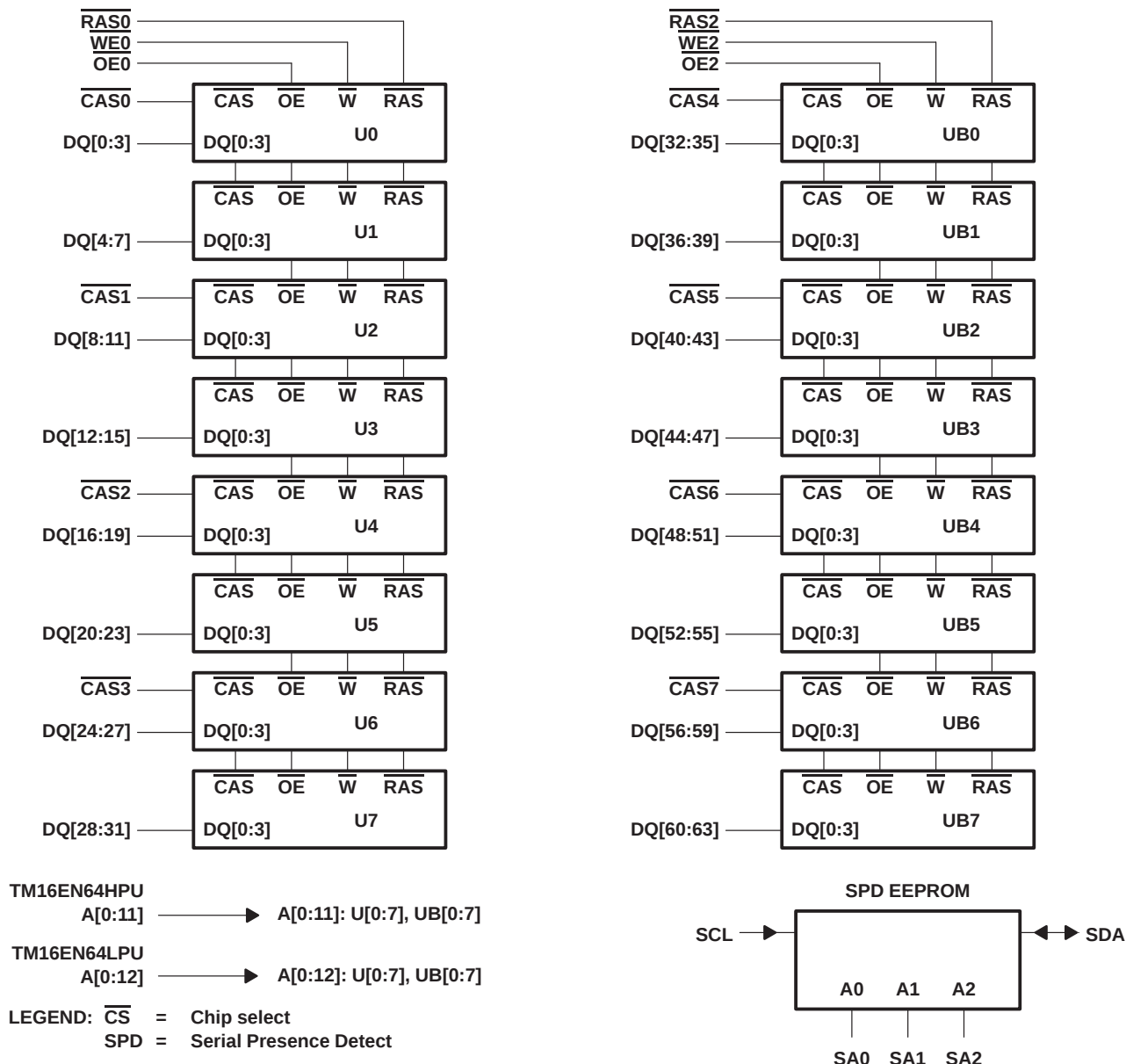
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dual-in-line memory module and components

The dual-in-line memory module and components include:

- PC substrate: 1,27 ± 0,1 mm (0.05 inch) nominal thickness; 0.005 inch/inch maximum warpage
- Bypass capacitors: Multilayer ceramic
- Contact area: Nickel plate and gold plate over copper

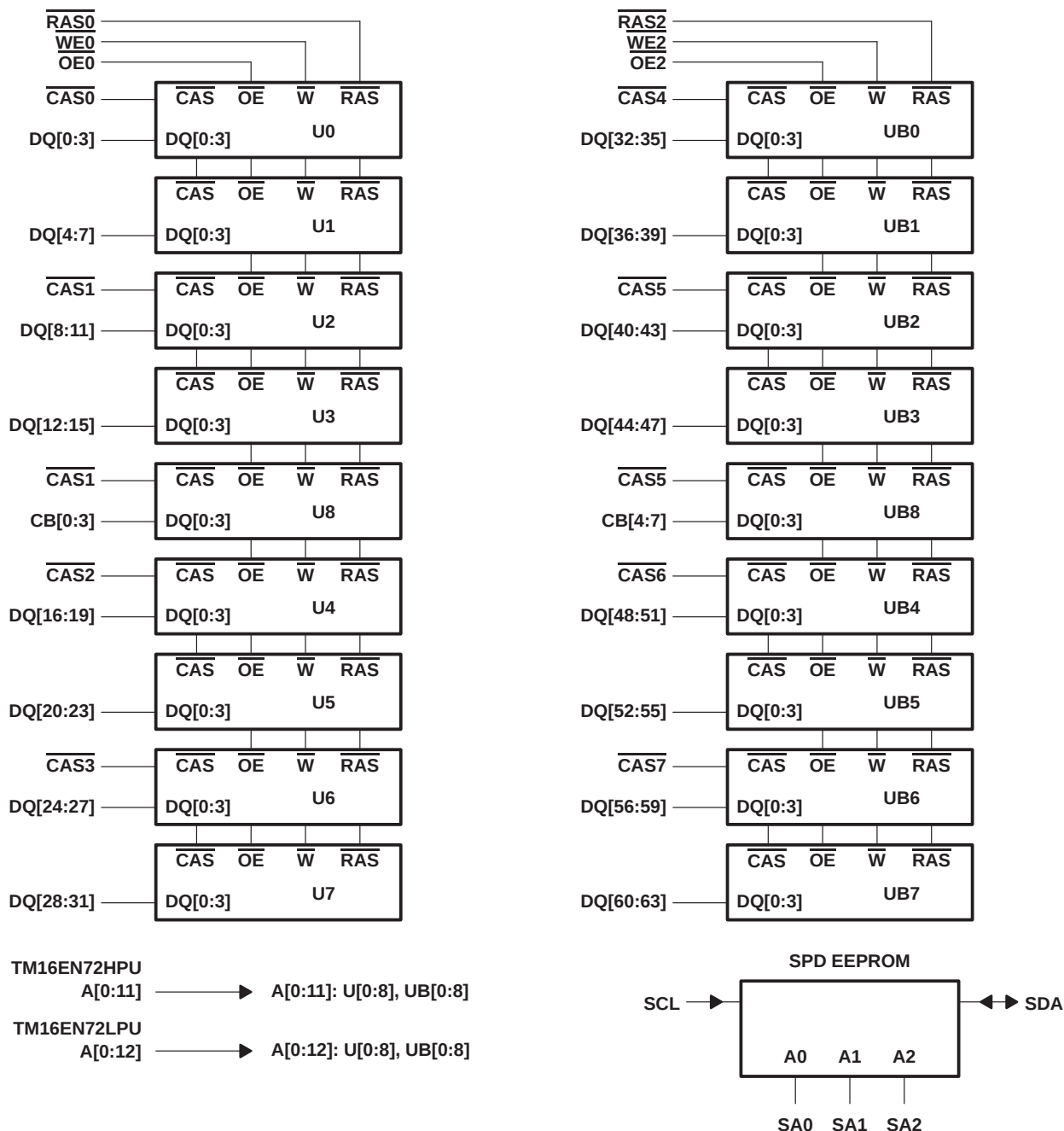
functional block diagram for the TM16EN64xPU



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functional block diagram for the TM16EN72xPU



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absolute maximum ratings over ambient temperature range (unless otherwise noted)[†]

Supply voltage range, V_{DD}	–0.5 V to 4.6 V
Voltage range on any pin (see Note 1)	– 0.5 V to 4.6 V
Short-circuit output current	50 mA
Power dissipation: TM16EN64xPU	16 W
TM16EN72xPU	18 W
Ambient temperature range, T_A	0°C to 70°C
Storage temperature range, T_{stg}	– 55°C to 125°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to V_{SS} .

recommended operating conditions

	MIN	NOM	MAX	UNIT
V_{DD} Supply voltage	3	3.3	3.6	V
V_{SS} Supply voltage		0		V
V_{IH} High-level input voltage	2		$V_{DD} + 0.3$	V
V_{IH-SPD} High-level input voltage for the SPD device	2		5.5	V
V_{IL} Low-level input voltage	–0.3		0.8	V
T_A Ambient temperature	0		70	°C

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electrical characteristics over recommended ranges of supply voltage and ambient temperature
(unless otherwise noted)

TM16EN64HPU

PARAMETER		TEST CONDITIONS†		'16EN64HPU-40		'16EN64HPU-50		'16EN64HPU-60		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
V _{OH}	High-level output voltage	I _{OH} = – 2 mA	LVTTL	2.4		2.4		2.4		V
		I _{OH} = – 100 µA	LVC MOS	V _{DD} – 0.2		V _{DD} – 0.2		V _{DD} – 0.2		
V _{OL}	Low-level output voltage	I _{OL} = 2 mA	LVTTL		0.4		0.4		0.4	V
		I _{OL} = 100 µA	LVC MOS		0.2		0.2		0.2	
I _I	Input current (leakage)	V _{DD} = 3.6 V, V _I = 0 V to 3.9 V, All others = 0 V to V _{DD}			± 20		± 20		± 20	µA
I _O	Output current (leakage)	V _{DD} = 3.6 V, V _O = 0 V to V _{DD} , CASx high			± 20		± 20		± 20	µA
I _{CC1} ‡§	Average read- or write-cycle current	V _{DD} = 3.6 V, Minimum cycle			2560		2080		1760	mA
I _{CC2}	Average standby current	V _{IH} = 2 V (LVTTL), After one memory cycle, RASx and CASx high			16		16		16	mA
		V _{IH} = V _{DD} – 0.2 V (LVC MOS), After one memory cycle, RASx and CASx high			8		8		8	mA
I _{CC3} ‡§	Average refresh current (RASx-only refresh or CBR)	V _{DD} = 3.6 V, Minimum cycle, RASx cycling, CASx high (RASx-only refresh), RASx low after CASx low (CBR)			2560		2080		1760	mA
I _{CC4} ‡¶	Average EDO current	V _{DD} = 3.6 V, RASx low, t _{HPC} = MIN, CASx cycling			2400		1920		1600	mA
I _{CC5} ‡¶	Average CBR refresh current	V _{DD} = 3.6 V, Minimum cycle, RASx low after CASx low			2560		2080		1760	mA

† For conditions shown as MIN/MAX, use the appropriate value specified in the timing requirements.

‡ Measured with outputs open

§ Measured with a maximum of one address change while RASx = V_{IL}

¶ Measured with a maximum of one address change during each EDO cycle, t_{HPC}

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**electrical characteristics over recommended ranges of supply voltage and ambient temperature
(unless otherwise noted) (continued)**

TM16EN64LPU

PARAMETER		TEST CONDITIONS [†]		'16EN64LPU-40		'16EN64LPU-50		'16EN64LPU-60		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
V _{OH}	High-level output voltage	I _{OH} = – 2 mA	LVTTL	2.4		2.4		2.4		V
		I _{OH} = – 100 µA	LVC MOS	V _{DD} – 0.2		V _{DD} – 0.2		V _{DD} – 0.2		
V _{OL}	Low-level output voltage	I _{OL} = 2 mA	LVTTL		0.4		0.4		0.4	V
		I _{OL} = 100 µA	LVC MOS		0.2		0.2		0.2	
I _I	Input current (leakage)	V _{DD} = 3.6 V, V _I = 0 V to 3.9 V, All others = 0 V to V _{DD}			± 20		± 20		± 20	µA
I _O	Output current (leakage)	V _{DD} = 3.6 V, V _O = 0 V to V _{DD} , CASx high			± 20		± 20		± 20	µA
I _{CC1} ^{‡§}	Average read- or write-cycle current	V _{DD} = 3.6 V, Minimum cycle			2000		1600		1440	mA
I _{CC2}	Average standby current	V _{IH} = 2 V (LVTTL), After one memory cycle, RASx and CASx high			16		16		16	mA
		V _{IH} = V _{DD} – 0.2 V (LVC MOS), After one memory cycle, RASx and CASx high			8		8		8	mA
I _{CC3} ^{‡§}	Average refresh current (RAS-only refresh or CBR)	V _{DD} = 3.6 V, Minimum cycle, RASx cycling, CASx high (RASx-only refresh), RASx low after CASx low (CBR)			2000		1600		1440	mA
I _{CC4} ^{‡¶}	Average EDO current	V _{DD} = 3.6 V, RASx low, t _{HPC} = MIN, CASx cycling			2240		1760		1440	mA
I _{CC5} ^{‡§}	Average CBR refresh current	V _{DD} = 3.6 V, Minimum cycle, RASx low after CASx low			2560		2080		1760	mA

[†] For conditions shown as MIN/MAX, use the appropriate value specified in the timing requirements.

[‡] Measured with outputs open

[§] Measured with a maximum of one address change while RASx = V_{IL}

[¶] Measured with a maximum of one address change during each EDO cycle, t_{HPC}

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electrical characteristics over recommended ranges of supply voltage and ambient temperature
(unless otherwise noted) (continued)

TM16EN72HPU

PARAMETER		TEST CONDITIONS [†]		'16EN72HPU-40		'16EN72HPU-50		'16EN72HPU-60		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
V _{OH}	High-level output voltage	I _{OH} = – 2 mA	LVTTL	2.4		2.4		2.4		V
		I _{OH} = – 100 µA	LVC MOS	V _{DD} – 0.2		V _{DD} – 0.2		V _{DD} – 0.2		
V _{OL}	Low-level output voltage	I _{OL} = 2 mA	LVTTL		0.4		0.4		0.4	V
		I _{OL} = 100 µA	LVC MOS		0.2		0.2		0.2	
I _I	Input current (leakage)	V _{DD} = 3.6 V, V _I = 0 V to 3.9 V, All others = 0 V to V _{DD}			± 20		± 20		± 20	µA
I _O	Output current (leakage)	V _{DD} = 3.6 V, V _O = 0 V to V _{DD} , CASx high			± 20		± 20		± 20	µA
I _{CC1} ^{‡§}	Average read- or write-cycle current	V _{DD} = 3.6 V, Minimum cycle			2880		2340		1980	mA
I _{CC2}	Average standby current	V _{IH} = 2 V (LVTTL), After one memory cycle, RASx and CASx high			18		18		36	mA
		V _{IH} = V _{DD} – 0.2 V (LVC MOS), After one memory cycle, RASx and CASx high			9		9		9	mA
I _{CC3} ^{‡§}	Average refresh current (RAS-only refresh or CBR)	V _{DD} = 3.6 V, Minimum cycle, RASx cycling, CASx high (RASx-only refresh), RASx low after CASx low (CBR)			2880		2340		1980	mA
I _{CC4} ^{‡¶}	Average EDO current	V _{DD} = 3.6 V, RASx low, t _{HPC} = MIN, CASx cycling			2700		2160		1800	mA
I _{CC5} ^{‡§}	Average CBR refresh current	V _{DD} = 3.6 V, Minimum cycle, RASx low after CASx low			2880		2340		1980	mA

[†] For conditions shown as MIN/MAX, use the appropriate value specified in the timing requirements.

[‡] Measured with outputs open

[§] Measured with a maximum of one address change while RASx = V_{IL}

[¶] Measured with a maximum of one address change during each EDO cycle, t_{HPC}

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**electrical characteristics over recommended ranges of supply voltage and ambient temperature
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TM16EN72LPU

PARAMETER		TEST CONDITIONS [†]		'16EN72LPU-40		'16EN72LPU-50		'16EN72LPU-60		UNIT
				MIN	MAX	MIN	MAX	MIN	MAX	
V _{OH}	High-level output voltage	I _{OH} = – 2 mA	LVTTL	2.4		2.4		2.4		V
		I _{OH} = – 100 µA	LVC MOS	V _{DD} – 0.2		V _{DD} – 0.2		V _{DD} – 0.2		
V _{OL}	Low-level output voltage	I _{OL} = 2 mA	LVTTL		0.4		0.4		0.4	V
		I _{OL} = 100 µA	LVC MOS		0.2		0.2		0.2	
I _I	Input current (leakage)	V _{DD} = 3.6 V, V _I = 0 V to 3.9 V, All others = 0 V to V _{DD}			± 20		± 20		± 20	µA
I _O	Output current (leakage)	V _{DD} = 3.6 V, V _O = 0 V to V _{DD} , CASx high			± 20		± 20		± 20	µA
I _{CC1} ^{‡§}	Average read- or write-cycle current	V _{DD} = 3.6 V, Minimum cycle			2250		1800		1620	mA
I _{CC2}	Average standby current	V _{IH} = 2 V (LVTTL), After one memory cycle, RASx and CASx high			18		18		18	mA
		V _{IH} = V _{DD} – 0.2 V (LVC MOS), After one memory cycle, RASx and CASx high			9		9		9	mA
I _{CC3} ^{‡§}	Average refresh current (RAS-only refresh or CBR)	V _{DD} = 3.6 V, Minimum cycle, RASx cycling, CASx high (RASx-only refresh), RASx low after CASx low (CBR)			2250		1800		1620	mA
I _{CC4} ^{‡¶}	Average EDO current	V _{DD} = 3.6 V, RASx low, t _{HPC} = MIN, CASx cycling			2520		1980		1620	mA
I _{CC5} ^{‡§}	Average CBR refresh current	V _{DD} = 3.6 V, Minimum cycle, RASx low after CASx low			2880		2340		1980	mA

[†] For conditions shown as MIN/MAX, use the appropriate value specified in the timing requirements.

[‡] Measured with outputs open

[§] Measured with a maximum of one address change while RASx = V_{IL}

[¶] Measured with a maximum of one address change during each EDO cycle, t_{HPC}

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capacitance over recommended ranges of supply voltage and ambient temperature,
f = 1 MHz (see Note 2)

PARAMETER		'16EN64xPU		'16EN72xPU		UNIT
		MIN	MAX	MIN	MAX	
C _{i(A)}	Input capacitance, A0 – A12		82		92	pF
C _{i(OE)}	Input capacitance, $\overline{\text{OEx}}$		58		65	pF
C _{i(CAS)}	Input capacitance, $\overline{\text{CASx}}$		16		23	pF
C _{i(RAS)}	Input capacitance, $\overline{\text{RASx}}$		58		65	pF
C _{i(W)}	Input capacitance, $\overline{\text{WEx}}$		58		65	pF
C _o	Output capacitance		8		8	pF

NOTE 2: V_{DD} = NOM supply voltage $\pm 10\%$, and the bias on pins under test is 0 V.

switching characteristics over recommended ranges of supply voltage and ambient temperature
(see Note 3)

PARAMETER		'16ENxxxPU-40		'16ENxxxPU-50		'16ENxxxPU-60		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{AA}	Access time from column address (see Note 4)		20		25		30	ns
t _{CAC}	Access time from $\overline{\text{CASx}}$ (see Note 4)		11		13		15	ns
t _{CPA}	Access time from $\overline{\text{CASx}}$ precharge (see Note 4)		22		28		35	ns
t _{RAC}	Access time from $\overline{\text{RASx}}$ (see Note 4)		40		50		60	ns
t _{OEa}	Access time from $\overline{\text{OEx}}$ (see Note 4)		11		13		15	ns
t _{CLZ}	Delay time, $\overline{\text{CASx}}$ to output in low impedance	0		0		0		ns
t _{REZ}	Output buffer turn off delay from $\overline{\text{RASx}}$ (see Note 5)	3	11	3	13	3	15	ns
t _{CEZ}	Output buffer turn off delay from $\overline{\text{CASx}}$ (see Note 5)	3	11	3	13	3	15	ns
t _{OEZ}	Output buffer turn off delay from $\overline{\text{OEx}}$ (see Note 5)	3	11	3	13	3	15	ns
t _{WEZ}	Output buffer turn off delay from $\overline{\text{WEx}}$ (see Note 5)	3	11	3	13	3	15	ns

NOTES: 3. With ac parameters, it is assumed that $t_T = 2$ ns.

4. Access times are measured with output reference levels of V_{OH} = 2 V and V_{OL} = 0.8 V.

5. The maximum values of t_{REZ}, t_{CEZ}, t_{OEZ}, and t_{WEZ} are specified when the output is no longer driven. Data in should not be driven until one of the applicable maximum specs is satisfied.

EDO timing requirements

		'16ENxxxPU-40		'16ENxxxPU-50		'16ENxxxPU-60		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{HPC}	Cycle time, EDO page mode, read-write		16		20		25	ns
t _{PRWC}	Cycle time, EDO read-write		47		57		68	ns
t _{CSH}	Delay time, $\overline{\text{RASx}}$ active to $\overline{\text{CASx}}$ precharge		32		40		48	ns
t _{CHO}	Hold time, $\overline{\text{OEx}}$ from $\overline{\text{CASx}}$		5		5		5	ns
t _{DOH}	Hold time, output from $\overline{\text{CASx}}$		5		5		5	ns
t _{CAS}	Pulse duration, $\overline{\text{CASx}}$ active (see Note 6)	6	10 000	8	10 000	10	10 000	ns
t _{WPE}	Pulse duration, $\overline{\text{WEx}}$ active (output disable only)	5		5		5		ns
t _{OCH}	Setup time, $\overline{\text{OEx}}$ before $\overline{\text{CASx}}$	5		5		5		ns
t _{CP}	Pulse duration, $\overline{\text{CASx}}$ precharge	6		8		10		ns
t _{OEP}	Precharge time, $\overline{\text{OEx}}$	5		5		5		ns

NOTE 6: In a read-write cycle, t_{CWD} and t_{CWL} must be observed.



**TM16EN64HPU, TM16EN64LPU 16777216 BY 64-BIT
TM16EN72HPU, TM16EN72LPU 16777216 BY 72-BIT
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ac timing requirements

		'16ENxxxPU-40		'16ENxxxPU-50		'16ENxxxPU-60		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{RC}	Cycle time, random read or write	69		84		104		ns
t _{RWC}	Cycle time, read-write	92		111		135		ns
t _{RASP}	Pulse duration, $\overline{\text{RASx}}$ active, fast page mode (see Note 7)	40	100 000	50	100 000	60	100 000	ns
t _{RAS}	Pulse duration, $\overline{\text{RASx}}$ active, non-page mode (see Note 7)	40	10 000	50	10 000	60	10 000	ns
t _{RP}	Pulse duration, $\overline{\text{RASx}}$ precharge	25		30		40		ns
t _{WP}	Pulse duration, write command	6		8		10		ns
t _{RASS}	Pulse duration, $\overline{\text{RASx}}$ active, self refresh (see Note 8)	100		100		100		μs
t _{RPS}	Pulse duration, $\overline{\text{RASx}}$ precharge after self refresh	70		90		110		ns
t _{ASC}	Setup time, column address	0		0		0		ns
t _{ASR}	Setup time, row address	0		0		0		ns
t _{DS}	Setup time, data in (see Note 9)	0		0		0		ns
t _{RCS}	Setup time, read command	0		0		0		ns
t _{CWL}	Setup time, write command before $\overline{\text{CASx}}$ precharge	6		8		10		ns
t _{RWL}	Setup time, write command before $\overline{\text{RASx}}$ precharge	6		8		10		ns
t _{WCS}	Setup time, write command before $\overline{\text{CASx}}$ active (early-write only)	0		0		0		ns
t _{WRP}	Setup time, $\overline{\text{WEx}}$ high before $\overline{\text{RASx}}$ low (CBR refresh only)	5		5		5		ns
t _{WTS}	Setup time, $\overline{\text{WEx}}$ low before $\overline{\text{RASx}}$ low (test mode only)	5		5		5		ns
t _{CSR}	Setup time, $\overline{\text{CASx}}$ referenced to $\overline{\text{RASx}}$ (CBR refresh only)	5		5		5		ns
t _{CAH}	Hold time, column address	6		8		10		ns
t _{DH}	Hold time, data in (see Note 9)	6		8		10		ns
t _{RAH}	Hold time, row address	6		8		10		ns
t _{RCH}	Hold time, read command referenced to $\overline{\text{CASx}}$ (see Note 10)	0		0		0		ns
t _{RRH}	Hold time, read command referenced to $\overline{\text{RASx}}$ (see Note 10)	0		0		0		ns
t _{WCH}	Hold time, write command during $\overline{\text{CASx}}$ active (early-write only)	6		8		10		ns
t _{ROH}	Hold time, $\overline{\text{RASx}}$ referenced to $\overline{\text{OEx}}$	6		8		10		ns
t _{WRH}	Hold time, $\overline{\text{WEx}}$ high after $\overline{\text{RASx}}$ low (CBR refresh)	6		8		10		ns
t _{WTH}	Hold time, $\overline{\text{WEx}}$ low after $\overline{\text{RASx}}$ low (test mode only)	6		8		10		ns
t _{CHR}	Hold time, $\overline{\text{CASx}}$ referenced to $\overline{\text{RASx}}$ (CBR refresh only)	6		8		10		ns
t _{OEH}	Hold time, $\overline{\text{OEx}}$ command	11		13		15		ns
t _{CHS}	Hold time, $\overline{\text{CASx}}$ active after $\overline{\text{RASx}}$ precharge (self-refresh)	–50		–50		–50		ns
t _{RHCP}	Hold time, $\overline{\text{RASx}}$ active from $\overline{\text{CASx}}$ precharge	22		28		35		ns

- NOTES: 7. In a read-write cycle, t_{RWD} and t_{RWL} must be observed.
8. During the period of 10 μs ≤ t_{RASS} ≤ 100 μs, the device is in transition state from normal operation mode to self-refresh mode.
9. Referenced to the later of $\overline{\text{CASx}}$ or $\overline{\text{WEx}}$ in write operations
10. Either t_{RRH} or t_{RCH} must be satisfied for a read cycle.

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TM16EN72HPU, TM16EN72LPU 16777216 BY 72-BIT
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ac timing requirements (continued)

		'16ENxxxPU-40		'16ENxxxPU-50		'16ENxxxPU-60		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	
t _{AWD}	Delay time, column address to write command (read-write only)	35		42		49		ns
t _{CPW}	Delay time, $\overline{WEx}$ low after $\overline{CASx}$ precharge (read-write only)	37		45		54		ns
t _{CRP}	Delay time, $\overline{CASx}$ precharge to $\overline{RASx}$	5		5		5		ns
t _{CWD}	Delay time, $\overline{CASx}$ to write command (read-write only)	26		30		34		ns
t _{OED}	Delay time, $\overline{OEx}$ to data in	11		13		15		ns
t _{RAD}	Delay time, $\overline{RASx}$ to column address (see Note 11)	8	20	10	25	12	30	ns
t _{RAL}	Delay time, column address to $\overline{RASx}$ precharge	20		25		30		ns
t _{CAL}	Delay time, column address to $\overline{CASx}$ precharge	12		15		18		ns
t _{RCD}	Delay time, $\overline{RASx}$ to $\overline{CASx}$ (see Note 11)	10	29	12	37	14	45	ns
t _{RPC}	Delay time, $\overline{RASx}$ precharge to $\overline{CASx}$	5		5		5		ns
t _{RSH}	Delay time, $\overline{CASx}$ active to $\overline{RASx}$ precharge	6		8		10		ns
t _{RWD}	Delay time, $\overline{RASx}$ to write command (read-write only)	55		67		79		ns
t _{TAA}	Access time from address (test mode)	25		30		35		ns
t _{TCPA}	Access time, from column precharge (test mode)	30		35		40		ns
t _{TRAC}	Access time, from $\overline{RASx}$ (test mode)	45		55		65		ns
t _T	Transition time	1	50	1	50	1	50	ns
t _{REF}	Refresh time interval		64		64		64	ms

NOTE 11: The maximum value is specified only to ensure access time.

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**TM16EN64HPU, TM16EN64LPU 16777216 BY 64-BIT
TM16EN72HPU, TM16EN72LPU 16777216 BY 72-BIT
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serial presence detect

The serial-presence-detect (SPD) is contained in a 2K-bit serial EEPROM located on the module. The SPD nonvolatile EEPROM contains various data such as module configuration, DRAM organization, and timing parameters (see tables below). Only the first 128 bytes are programmed by Texas Instruments, while the remaining 128 bytes are available for customer use. Programming is done through a IIC bus using the clock (SCL) and data (SDA) signals. All Texas Instruments modules comply with the current JEDEC SPD Standard. See the *Texas Instruments Serial Presence Detect Technical Reference* (literature number SMMU001) for further details.

Tables in this section list the SPD contents as follows:

Table 1–TM16EN64HPU

Table 2–TM16EN64LPU

Table 3–TM16EN72HPU

Table 4–TM16EN72LPU

Table 1. Serial-Presence-Detect Data for the TM16EN64HPU

BYTE NO.	FUNCTION DESCRIBED	'16EN64HPU-40		'16EN64HPU-50		'16EN64HPU-60	
		ITEM	DATA	ITEM	DATA	ITEM	DATA
0	Defines number of bytes written into serial memory during module manufacturing	128 bytes	80h	128 bytes	80h	128 bytes	80h
1	Total number of bytes of SPD memory device	256 bytes	08h	256 bytes	08h	256 bytes	08h
2	Fundamental memory type (FPM, EDO, SDRAM)	EDO	02h	EDO	02h	EDO	02h
3	Number of row addresses on this assembly	12	0Ch	12	0Ch	12	0Ch
4	Number of column addresses on this assembly	12	0Ch	12	0Ch	12	0Ch
5	Number of module banks on this assembly	1 bank	01h	1 bank	01h	1 bank	01h
6	Data width of this assembly	64 bits	40h	64 bits	40h	64 bits	40h
7	Data width continuation		00h		00h		00h
8	Voltage interface standard of this assembly	LVTTL	01h	LVTTL	01h	LVTTL	01h
9	RASx access time of module	t _{RAC} =40ns	28h	t _{RAC} =50ns	32h	t _{RAC} =60ns	3Ch
10	CASx access time of module	t _{CAC} =11ns	0Bh	t _{CAC} =13ns	0Dh	t _{CAC} =15ns	0Fh
11	DIMM configuration type (non-parity, parity, ECC)	Non-parity	00h	Non-parity	00h	Non-parity	00h
12	Refresh rate/type	15.6 μ s	00h	15.6 μ s	00h	15.6 μ s	00h
13	DRAM width, primary DRAM	x4	04h	x4	04h	x4	04h
14	Error-checking SDRAM data width	N/A	00h	N/A	00h	N/A	00h
62	SPD revision	Rev. 1	01h	Rev. 1	01h	Rev. 1	01h
63	Checksum for bytes 0–62	26	1Ah	38	26h	50	32h
64–71	Manufacturer's JEDEC ID code per JEP-106E	97h	9700...00h	97h	9700...00h	97h	9700...00h
72	Manufacturing location [†]	TBD		TBD		TBD	
73–90	Manufacturer's part number [†]	TBD		TBD		TBD	
91	Die revision code [†]	TBD		TBD		TBD	

[†] TBD indicates values are determined at manufacturing time and are module dependent.

serial presence detect (continued)

Table 1. Serial Presence-Detect Data for the TM16EN64HPU (Continued)

BYTE NO.	FUNCTION DESCRIBED	'16EN64HPU-40		'16EN64HPU-50		'16EN64HPU-60	
		ITEM	DATA	ITEM	DATA	ITEM	DATA
95–98	Assembly serial number [†]	TBD		TBD		TBD	
92	PCB revision code [†]	TBD		TBD		TBD	
93–94	Manufacturing date [†]	TBD		TBD		TBD	
99–125	Manufacturer specific data [†]	TBD		TBD		TBD	
126–127	Vendor specific data [†]	TBD		TBD		TBD	
128–166	System integrator's specific data [‡]	TBD		TBD		TBD	
167–255	Open						

[†] TBD indicates values are determined at manufacturing time and are module dependent.

[‡] These TBD values are determined and programmed by the customer (optional).

**TM16EN64HPU, TM16EN64LPU 16777216 BY 64-BIT
TM16EN72HPU, TM16EN72LPU 16777216 BY 72-BIT
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serial presence detect (continued)

Table 2. Serial-Presence-Detect Data for the TM16EN64LPU

BYTE NO.	FUNCTION DESCRIBED	'16EN64LPU-40		'16EN64LPU-50		'16EN64LPU-60	
		ITEM	DATA	ITEM	DATA	ITEM	DATA
0	Defines number of bytes written into serial memory during module manufacturing	128 bytes	80h	128 bytes	80h	128 bytes	80h
1	Total number of bytes of SPD memory device	256 bytes	08h	256 bytes	08h	256 bytes	08h
2	Fundamental memory type (FPM, EDO, SDRAM)	EDO	02h	EDO	02h	EDO	02h
3	Number of row addresses on this assembly	13	0Dh	13	0Dh	13	0Dh
4	Number of column addresses on this assembly	11	0Bh	11	0Bh	11	0Bh
5	Number of module banks on this assembly	1 bank	01h	1 bank	01h	1 bank	01h
6	Data width of this assembly	64 bits	40h	64 bits	40h	64 bits	40h
7	Data width continuation		00h		00h		00h
8	Voltage interface standard of this assembly	LVTTL	01h	LVTTL	01h	LVTTL	01h
9	RASx access time of module	t _{RAC} =40ns	28h	t _{RAC} =50ns	32h	t _{RAC} =60ns	3Ch
10	CASx access time of module	t _{CAC} =11ns	0Bh	t _{CAC} =13ns	0Dh	t _{CAC} =15ns	0Fh
11	DIMM configuration type (non-parity, parity, ECC)	Non-Parity	00h	Non-Parity	00h	Non-parity	00h
12	Refresh rate/type	15.6 μs	00h	15.6 μs	00h	15.6 μs	00h
13	DRAM width, primary DRAM	x4	04h	x4	04h	x4	04h
14	Error-checking SDRAM data width	N/A	00h	N/A	00h	N/A	00h
62	SPD revision	Rev. 1	01h	Rev. 1	01h	Rev. 1	01h
63	Checksum for bytes 0–62	36	1Ah	38	26h	50	32h
64–71	Manufacturer's JEDEC ID code per JEP-106E	97h	9700...00h	97h	9700...00h	97h	9700...00h
72	Manufacturing location [†]	TBD		TBD		TBD	
73–90	Manufacturer's part number [†]	TBD		TBD		TBD	
91	Die revision code [†]	TBD		TBD		TBD	
92	PCB revision code [†]	TBD		TBD		TBD	
93–94	Manufacturing date [†]	TBD		TBD		TBD	
95–98	Assembly serial number [†]	TBD		TBD		TBD	
99–125	Manufacturer specific data [†]	TBD		TBD		TBD	
126–127	Vendor specific data [†]	TBD		TBD		TBD	
128–166	System integrator's specific data [‡]	TBD		TBD		TBD	
167–255	Open						

[†] TBD indicates values are determined at manufacturing time and are module dependent.

[‡] These TBD values are determined and programmed by the customer (optional).

serial presence detect (continued)

Table 3. Serial-Presence-Detect Data for the TM16EN72HPU

BYTE NO.	FUNCTION DESCRIBED	'16EN72HPU-40		'16EN72HPU-50		'16EN72HPU-60	
		ITEM	DATA	ITEM	DATA	ITEM	DATA
0	Defines number of bytes written into serial memory during module manufacturing	128 bytes	80h	128 bytes	80h	128 bytes	80h
1	Total number of bytes of SPD memory device	256 bytes	08h	256 bytes	08h	256 bytes	08h
2	Fundamental memory type (FPM, EDO, SDRAM)	EDO	02h	EDO	02h	EDO	02h
3	Number of row addresses on this assembly	12	0Ch	12	0Ch	12	0Ch
4	Number of column addresses on this assembly	12	0Ch	12	0Ch	12	0Ch
5	Number of module banks on this assembly	1 bank	01h	1 bank	01h	1 bank	01h
6	Data width of this assembly	72 bits	48h	72 bits	48h	72 bits	48h
7	Data width continuation		00h		00h		00h
8	Voltage interface standard of this assembly	LVTTL	01h	LVTTL	01h	LVTTL	01h
9	RASx access time of module	t _{RAC} =40ns	28h	t _{RAC} =50ns	32h	t _{RAC} =60ns	3Ch
10	CASx access time of module	t _{CAC} =11ns	0Bh	t _{CAC} =13ns	0Dh	t _{CAC} =15ns	0Fh
11	DIMM configuration type (non-parity, parity, ECC)	ECC	02h	ECC	02h	ECC	02h
12	Refresh rate/type	15.6 μs	00h	15.6 μs	00h	15.6 μs	00h
13	DRAM width, primary DRAM	x4	04h	x4	04h	x4	04h
14	Error-checking SDRAM data width	x4	04h	x4	04h	x4	04h
62	SPD revision	Rev. 1	01h	Rev. 1	01h	Rev. 1	01h
63	Checksum for bytes 0–62	40	28h	52	34h	64	40h
64–71	Manufacturer's JEDEC ID code per JEP-106E	97h	9700...00h	97h	9700...00h	97h	9700...00h
72	Manufacturing location [†]	TBD		TBD		TBD	
73–90	Manufacturer's part number [†]	TBD		TBD		TBD	
91	Die revision code [†]	TBD		TBD		TBD	
92	PCB revision code [†]	TBD		TBD		TBD	
93–94	Manufacturing date [†]	TBD		TBD		TBD	
95–98	Assembly serial number [†]	TBD		TBD		TBD	
99–125	Manufacturer specific data [†]	TBD		TBD		TBD	
126–127	Vendor specific data [†]	TBD		TBD		TBD	
128–166	System integrator's specific data [‡]	TBD		TBD		TBD	
167–255	Open						

[†] TBD indicates values are determined at manufacturing time and are module dependent.

[‡] These TBD values are determined and programmed by the customer (optional).

**TM16EN64HPU, TM16EN64LPU 16777216 BY 64-BIT
TM16EN72HPU, TM16EN72LPU 16777216 BY 72-BIT
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serial presence detect (continued)

Table 4. Serial-Presence-Detect Data for the TM16EN72LPU

BYTE NO.	FUNCTION DESCRIBED	'16EN72LPU-40		'16EN72LPU-50		'16EN72LPU-60	
		ITEM	DATA	ITEM	DATA	ITEM	DATA
0	Defines number of bytes written into serial memory during module manufacturing	128 bytes	80h	128 bytes	80h	128 bytes	80h
1	Total number of bytes of SPD memory device	256 bytes	08h	256 bytes	08h	256 bytes	08h
2	Fundamental memory type (FPM, EDO, SDRAM)	EDO	02h	EDO	02h	EDO	02h
3	Number of row addresses on this assembly	13	0Dh	13	0Dh	13	0Dh
4	Number of column addresses on this assembly	11	0Bh	11	0Bh	11	0Bh
5	Number of module banks on this assembly	1 bank	01h	1 bank	01h	1 bank	01h
6	Data width of this assembly	72 bits	48h	72 bits	48h	72 bits	48h
7	Data width continuation		00h		00h		00h
8	Voltage interface standard of this assembly	LVTTL	01h	LVTTL	01h	LVTTL	01h
9	RASx access time of module	t _{RAC} =40ns	28h	t _{RAC} =50ns	32h	t _{RAC} =60ns	3Ch
10	CASx access time of module	t _{CAC} =11ns	0Bh	t _{CAC} =13ns	0Dh	t _{CAC} =15ns	0Fh
11	DIMM configuration type (non-parity, parity, ECC)	ECC	02h	ECC	02h	ECC	02h
12	Refresh rate/type	15.6 μs	00h	15.6 μs	00h	15.6 μs	00h
13	DRAM width, primary DRAM	x4	04h	x4	04h	x4	04h
14	Error-checking SDRAM data width	x4	04h	x4	04h	x4	04h
62	SPD revision	Rev. 1	01h	Rev. 1	01h	Rev. 1	01h
63	Checksum for bytes 0–62	40	28h	52	34h	64	40h
64–71	Manufacturer's JEDEC ID code per JEP-106E	97h	9700...00h	97h	9700...00h	97h	9700...00h
72	Manufacturing location [†]	TBD		TBD		TBD	
73–90	Manufacturer's part number [†]	TBD		TBD		TBD	
91	Die revision code [†]	TBD		TBD		TBD	
92	PCB revision code [†]	TBD		TBD		TBD	
93–94	Manufacturing date [†]	TBD		TBD		TBD	
95–98	Assembly serial number [†]	TBD		TBD		TBD	
99–125	Manufacturer specific data [†]	TBD		TBD		TBD	
126–127	Vendor specific data [†]	TBD		TBD		TBD	
128–166	System integrator's specific data [‡]	TBD		TBD		TBD	
167–255	Open						

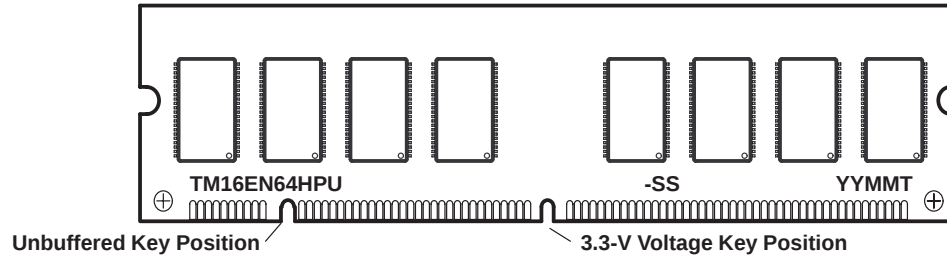
[†] TBD indicates values are determined at manufacturing time and are module dependent.

[‡] These TBD values are determined and programmed by the customer (optional).

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device symbolization (TM16EN64HPU illustrated)



YY = Year Code
MM = Month Code
T = Assembly Site Code
-SS = Speed Code

NOTE A: Location of symbolization may vary.

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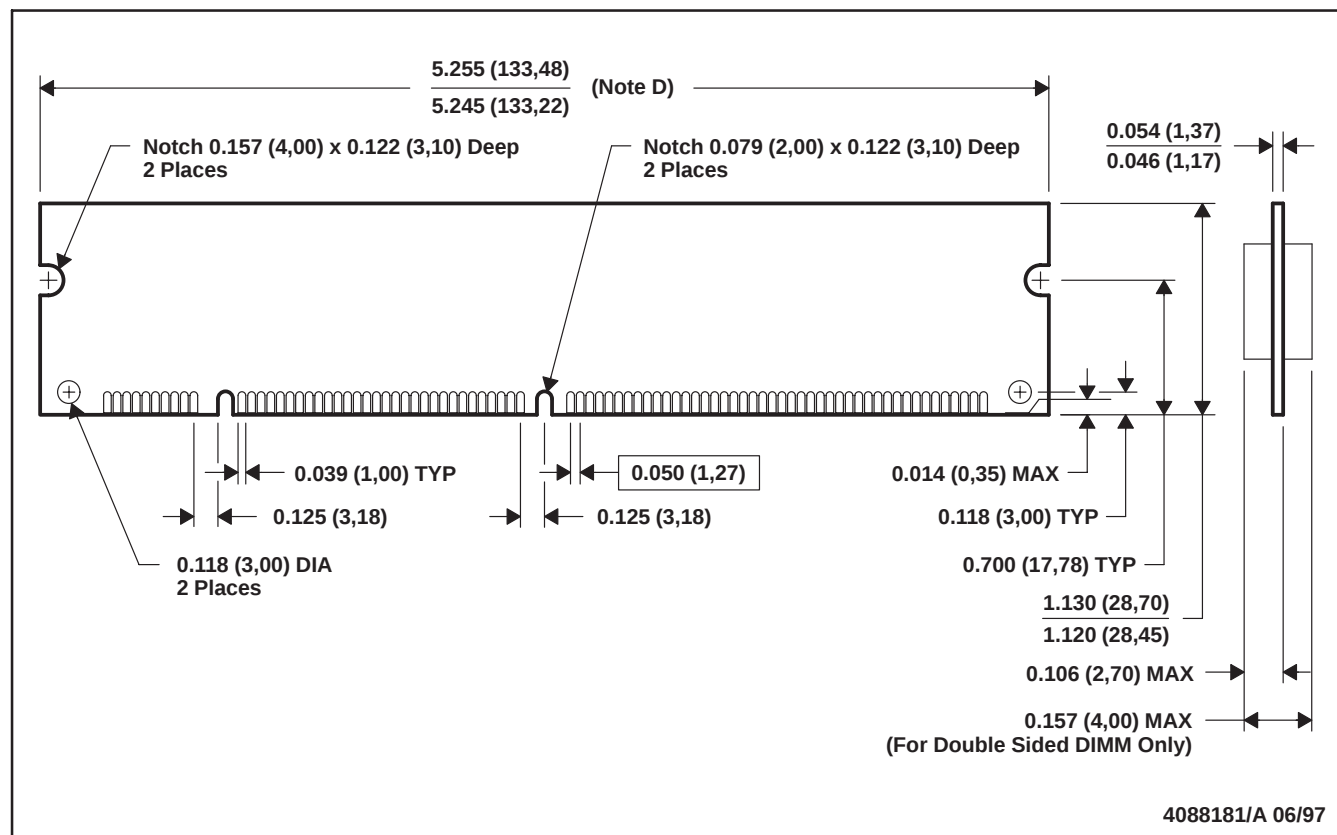
TM16EN64HPU, TM16EN64LPU 16777216 BY 64-BIT
 TM16EN72HPU, TM16EN72LPU 16777216 BY 72-BIT
 EXTENDED-DATA-OUT DYNAMIC RAM MODULES

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MECHANICAL DATA

BS (R-PDIM-N168)

DUAL IN-LINE MEMORY MODULE



- NOTES: A. All linear dimensions are in inches (millimeters).
 B. This drawing is subject to change without notice.
 C. Falls within JEDEC MO-161
 D. Dimension includes De-panelization variations; applies between notch and tab edge.
 E. Outline may vary above notches to allow router/panelization irregularities.

PRODUCT PREVIEW

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